

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLV21** is Designed for Class C, 28 V High Band Applications up to 175 MHz.

FEATURES:

- Common Emitter
- $P_G = 10$ dB at 15 W/175 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	1.75 A
V_{CEO}	35 V
V_{CES}	65 V
V_{EBO}	4.0 V
P_{DISS}	36 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	4.8 °C/W

PACKAGE STYLE .380 4L FLG

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

ORDER CODE: ASI10579

CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 25$ mA			35			V
BV_{CES}	$I_C = 5.0$ mA			65			V
BV_{EBO}	$I_E = 10$ mA			4.0			V
I_{CBO}	$V_{CB} = 30$ V					1.0	mA
h_{FE}	$V_{CE} = 5.0$ V	$I_C = 200$ mA		5.0		---	---
C_{OB}	$V_{CB} = 30$ V	$f = 1.0$ MHz				50	pF
P_G	$V_{CC} = 28$ V	$P_{OUT} = 15$ W	$f = 175$ MHz	10			dB
η_C				65			%